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Vishay Semiconductors

RoHS

HALOGEN

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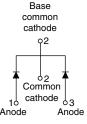
Hyperfast Rectifier, 2 x 15 FRED Pt®





TO-220AB

TO-220 FULL-PAK





VS-30CTH02PbF VS-30CTH02-N3

VS-30CTH02FPPbF VS-30CTH02FP-N3

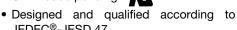
PRODUCT SUMMARY				
Package	TO-220AB, TO-220FP			
I _{F(AV)}	2 x 15 A			
V_{R}	200 V			
V _F at I _F	0.78 V			
t _{rr} typ.	See Recovery table			
T _J max.	175 °C			
Diode variation	Common cathode			

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending

JEDEC®-JESD 47







DESCRIPTION / APPLICATIONS

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage		V _{RRM}		200	V	
	per diode		T _C = 159 °C	15		
Average rectified forward current	(FULL-PAK) per diode	I _{F(AV)}	T _C = 125 °C	15		
	per device			30	А	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	200			
Operating junction and storage ten	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-		
Forward voltage V _F	W	I _F = 15 A	-	0.92	1.05	V	
	v _F	I _F = 15 A, T _J = 125 °C	-	0.78	0.85		
Reverse leakage current I _R		V _R = V _R rated	-	-	10		
		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	5	300	μA	
Junction capacitance	C _T	V _R = 200 V - 57		-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8 -		nH			



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A, } dI_F/dt = 50 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	-	35	
Reverse recovery time	t _{rr}	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	30	
		T _J = 25 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	26	-	ns A
		T _J = 125 °C		-	40	-	
Peak recovery current		T _J = 25 °C		-	2.8	-	
	IRRM	T _J = 125 °C	11	-	6.0	-	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	37	-	200
	Q _{rr}	T _J = 125 °C		-	120	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction ar temperature range	nd storage	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance,	per diode	R _{th.IC}	Mounting surface, flat, smooth and greased	-	-	1.1	°C/W
junction to case	(FULL-PAK) per diode			-	-	3.5	O/ VV
Marking device			Case style TO-220AB		30CTH02		
			Case style TO-220 FULL-PAK		30CTI	H02FP	

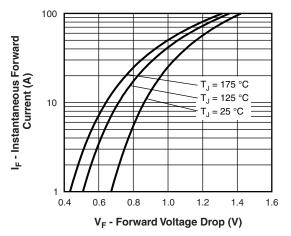


Fig. 1 - Typical Forward Voltage Drop Characteristics

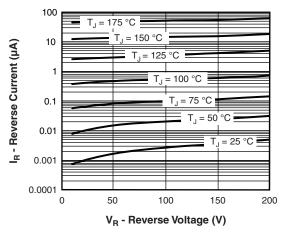


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



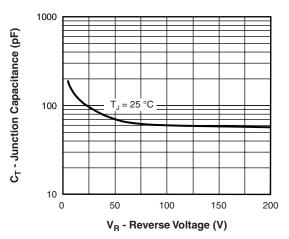


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

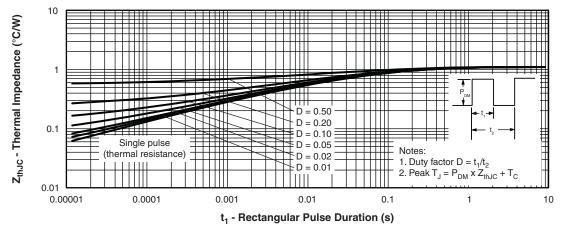


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

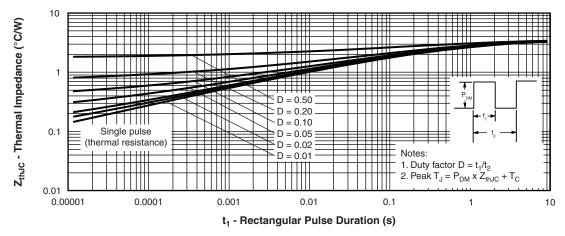


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)



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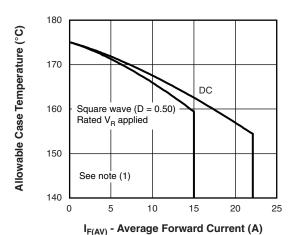


Fig. 6 - Maximum Allowable Case Temperature vs.
Average Forward Current

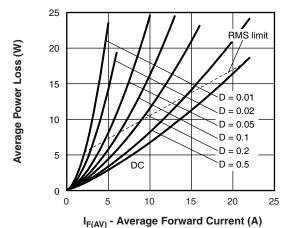


Fig. 8 - Forward Power Loss Characteristics

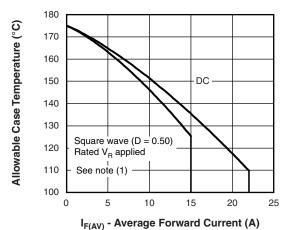


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

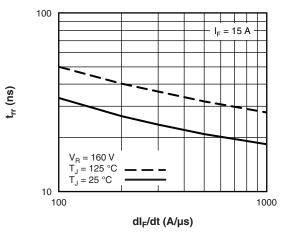


Fig. 9 - Typical Reverse Recovery Time vs. dl_F/dt

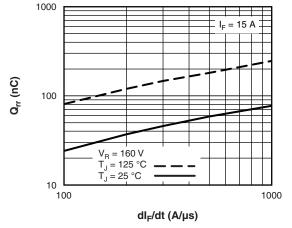


Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

(1) Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 8); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R

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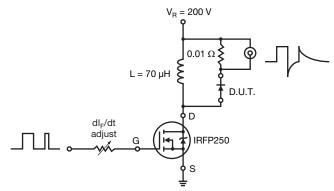
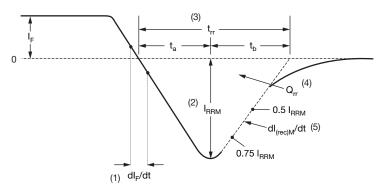


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{r}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

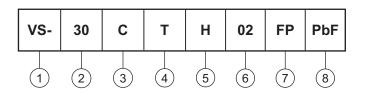
(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (30 = 30 A)

3 - C = common cathode

4 - T = TO-220

5 - H = hyperfast recovery

Voltage rating (02 = 200 V)

7 - • None = TO-220AB

• FP = TO-220 FULL-PAK

8 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

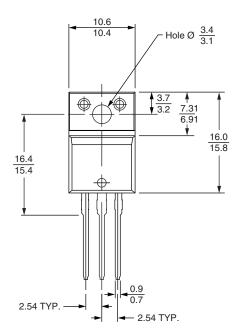
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-20CTH03PbF	50	1000	Antistatic plastic tube		
VS-20CTH03-N3	50	1000	Antistatic plastic tube		
VS-20CTH03FPPbF	50	1000	Antistatic plastic tube		
VS-20CTH03FP-N3	50	1000	Antistatic plastic tube		

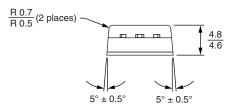
LINKS TO RELATED DOCUMENTS					
Dimensions	TO-220AB	www.vishay.com/doc?95222			
Dimensions	TO-220FP	www.vishay.com/doc?95072			
Part marking information	TO-220ABPbF	www.vishay.com/doc?95225			
	TO-220AB-N3	www.vishay.com/doc?95028			
	TO-220FPPbF	www.vishay.com/doc?95069			
	TO-220FP-N3	www.vishay.com/doc?95456			

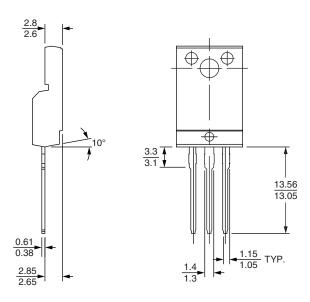


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DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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